

Silicon PNP Power Transistors

BD234 BD236 BD238

DESCRIPTION

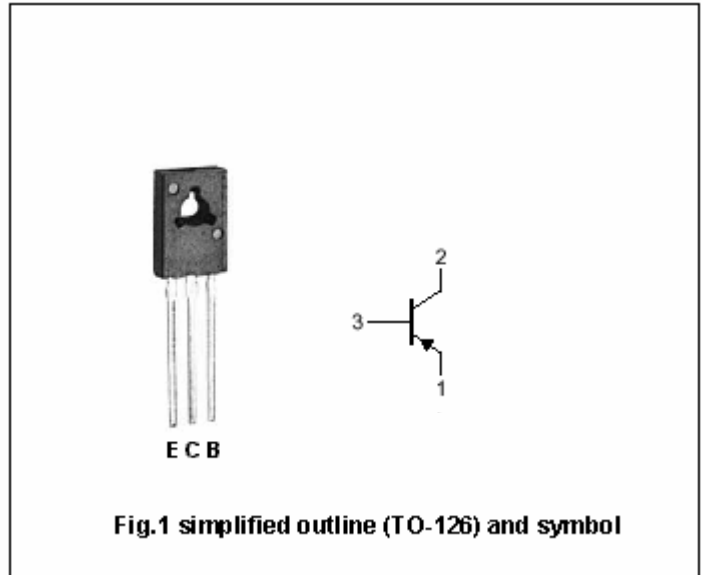
- With TO-126 package
- Complement to type BD233/235 /237

APPLICATIONS

- For medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	BD234	-45	V
		BD236	-60	
		BD238	-100	
V _{CEO}	Collector-emitter voltage	BD234	-45	V
		BD236	-60	
		BD238	-80	
V _{EBO}	Emitter -base voltage	Open collector	-5	V
I _C	Collector current (DC)		-2	A
I _{CM}	Collector current-Peak		-6	A
P _C	Collector power dissipation	T _C =25℃	25	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-65~150	℃

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-0.6	V	
V _{BE}	Base-emitter on voltage	I _C =-1A; V _{CE} =-2V			-1.3	V	
V _{CEO(SUS)}	Collector-emitter sustaining voltage	BD234	I _C =-0.1A; I _B =0	-45		V	
		BD236		-60			
		BD238		-80			
I _{CBO}	Collector cut-off current	BD234			-100	μA	
		BD236					V _{CB} =-60V; I _E =0
		BD238					V _{CB} =-100V; I _E =0
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1	mA	
h _{FE-1}	DC current gain	I _C =-150mA; V _{CE} =-2V	40				
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-2V	25				
f _T	Transition frequency	I _C =-250mA; V _{CE} =-10V	3			MHz	

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PACKAGE OUTLINE

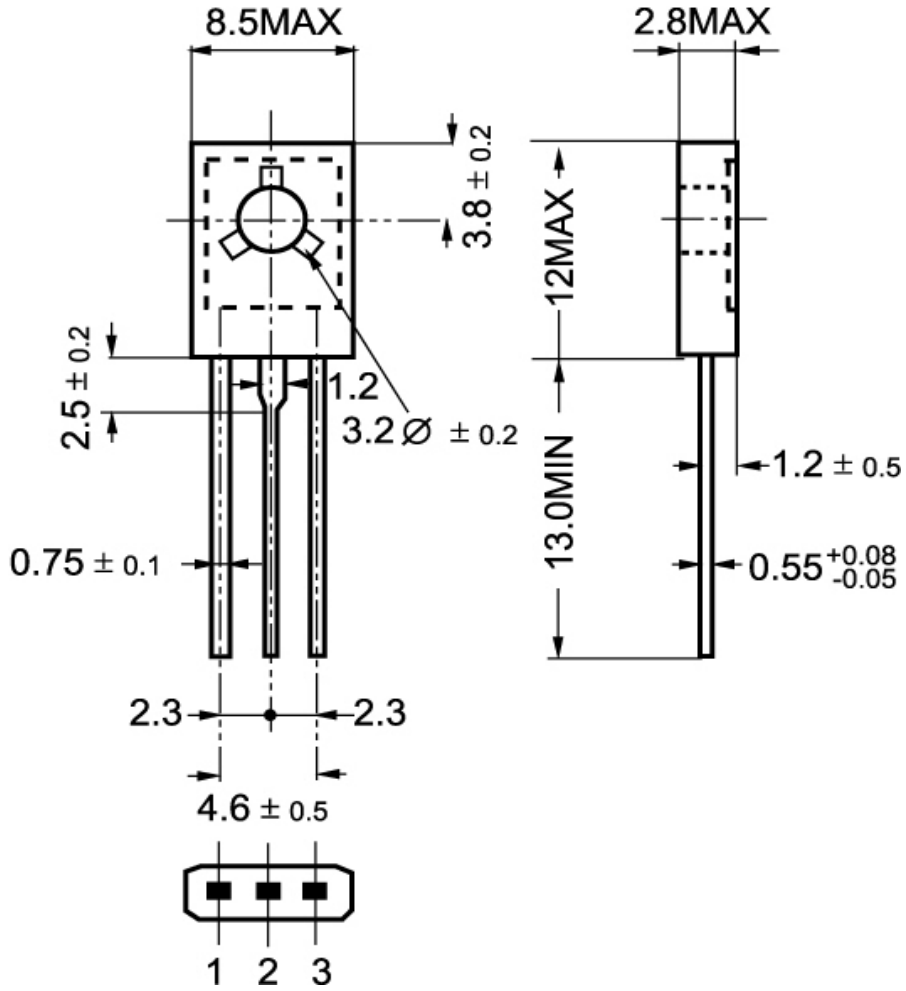


Fig.2 Outline dimensions